

<b>Notice of References Cited</b>	Application/Control No. 10/516,380		Applicant(s)/Patent Under Reexamination MAKIMOTO ET AL.	
	Examiner TRAM H. NGUYEN		Art Unit 2818	Page 1 of 1

#### U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,313,488	11-2001	Bakowski et al.	257/198
*	B	US-2002/0195619	12-2002	Makimoto et al.	257/197
	C	US-			
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	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

#### FOREIGN PATENT DOCUMENTS

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#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	K. Kumakura, T. Makimoto and N. Kobayashi, Low-Resistance Nonalloyed Ohmic Contact to p-type GaN Using Strained InGaN Contact Layer, Applied Physics Letters, Vol. 79, No. 16, pp 2588-2590 (2001).
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.